

Asymmetric GTO Thyristors

- Free-floating silicon
- High-dynamic voltage capability at turn-off
- Low on-state and switching losses
- Coaxial gate leads soldered
- Reverse avalanche capability

Asymmetrische GTO Thyristoren

- Freier Druckkontakt
- Hohe dynamische Spannungsfestigkeit beim Ausschalten
- Geringe Schaltverluste
- Koaxiales Gate-Kabel angelötet
- Avalanche-Eigenschaften in Sperrichtung

Thyristors GTO asymétriques

T25-20

- Contact par pression directe
- Tenue en tension dynamique élevée à l'extinction
- Faible perte de puissance
- Câble de gâchette coaxial soudé
- Caractéristique "avalanche" en sens inverse

Ordering number Bestellnummer Num. de commande	V _{DRM} V	V _{RRM} V _{GRRM} V	I _{TGQM} A	C _s µF	I _{TAVM} T _C =85° A	I _{TSM} (T _{VJM}) 10 ms kA	V _T (I _T = I _{TGQM}) V	I _{GT} A	T _{VJM} °C	R _{thJC} K/W	F kN	Fig. No.	Datasheet Datenblatt Feuille technique
YS 550 101 XX P14...P24	1400...2400	18	700	1	305	5	2.5	0.8	125	0.05	7	33	YSG 701
YS 570 102 XX P14...P24	1400...2400	18	1000	2	550	10	2.3	1.5	125	0.03	16	34	YSG 1000
YS 570 101 XX P14...P24	1400...2400	18	1500	3	550	10	2.5	1.5	125	0.03	16	34	YSG 1500
YS 580 102 XX P14...P24	1400...2400	18	2000	4	1040	16	2.5	3	125	0.015	22	35	YSG 2000
YS 580 104 XX P14...P24	1400...2400	18	2000	4	1040	16	2.5	3	125	0.015	22	36	YSG 2001
YS 580 101 XX P14...P24	1400...2400	18	2500	6	1040	17	2.7	3	125	0.015	33	35	YSG 2500
YS 580 103 XX P14...P24	1400...2400	18	2500	6	1040	17	2.7	3	125	0.015	33	36	YSG 2501
CSG 601-25A01	2500	18	600	1	300	3	3	0.8	125	0.04	11	37	CH-4UH 90006E
CSG 2001-25A01	2500	17	2000	4	830	16	2.8	2.5	125	0.017	22	38	CH-4UH 90005E
CSG 2501-25A01	2500	17	2500	6	830	16	3.1	2.5	125	0.017	22	38	CH-4UH 90009E
CSG 603-45A01	4500	17	600	1	170	2.5	4.5	1.5	125	0.05	11	39	CH-4UH 90010E
CSG 2003-45A01	4500	17	2000	4	640	13	3.5	2.5	125	0.02	22	38	CH-4UH 90011E
CSG 3003-45A01	4500	17	3000	6	790	24	4	4	125	0.015	40	40	CH-4UH 90008E

Reverse Conducting GTO Thyristors

- Monolithic integration of GTO and freewheeling diode
- Small size and less weight
- Low on-state and switching losses
- Coaxial gate leads
- less induction losses

Rückwärtsleitende GTO Thyristoren

- GTO-Thyristor und Freilaufdiode auf einer Siliziumtablette
- Platz- und Gewichtsersparnis
- Geringe Schaltverluste
- Koaxiales Gate-Kabel
- Geringe Induktionsverluste

Thyristors GTO à conduction inverse

- Intégration monolithique d'un thyristor GTO et d'une diode à roue libre
- Economie de place et de poids
- Faible pert de puissance
- Câble de gâchette coaxial
- Faible perte d'induction

Type Ordering number Bestellnummer Num. de commande	V _{DRM} V	V _{GRM} V	I _{TGQM} A	C _s µF	I _{TAVM} T _C =85° A	I _{TSM} (T _{VJM}) 10 ms kA	V _T (I _T = I _{TGQM}) V	I _{GT} A	T _{VJM} °C	R _{thJC} K/W	F kN	Fig. No.	Datasheet Datenblatt Feuille technique
CRG 2001-25A01	2500	17	2000	3	700	14	3.5	2.5	125	0.017	40	40	
CRG 2003-45A01	4500	17	2000	4	520	11	4.4	2.5	125	0.02	40	40	

T-25-20

Dimensions in mm

A = Anode
K = Cathode
G = Gate
HK = Auxiliary cathode

Abmessungen in mm

A = Anode
K = Kathode
G = Gate
HK = Hilfskathode

Dimensions en mm

A = Anode
K = Cathode
G = Gâchette
HK = Cathode auxiliaire

Fig. 33

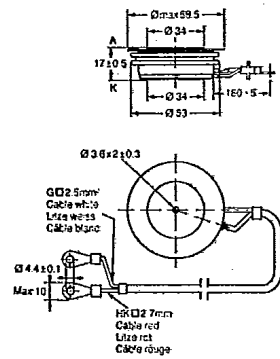


Fig. 36

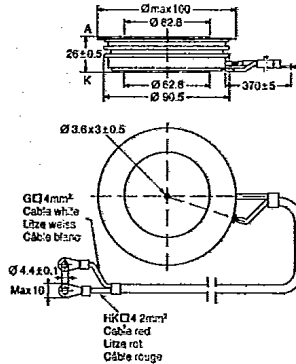


Fig. 39

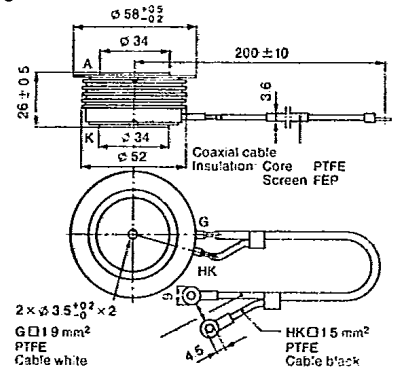


Fig. 34

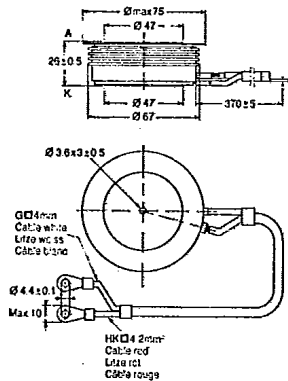


Fig. 37

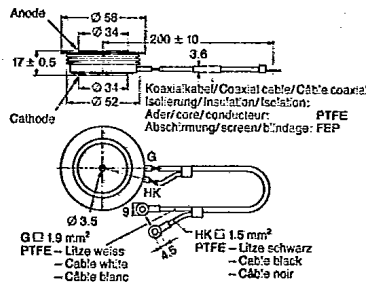


Fig. 40

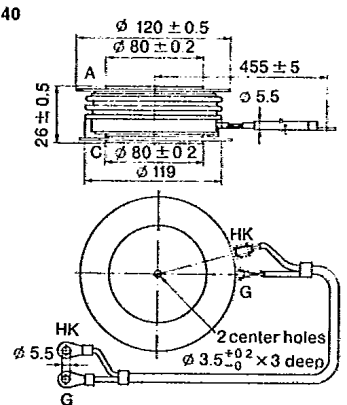


Fig. 35

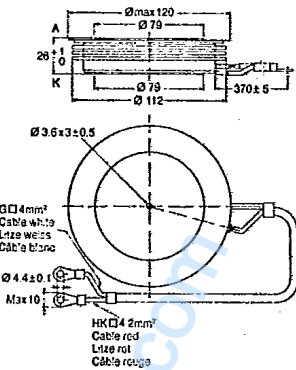


Fig. 38

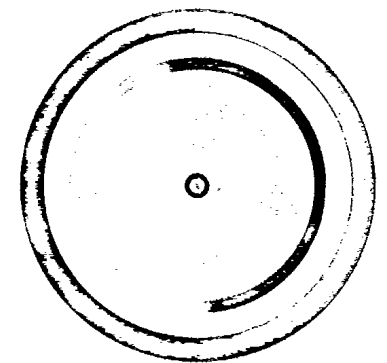
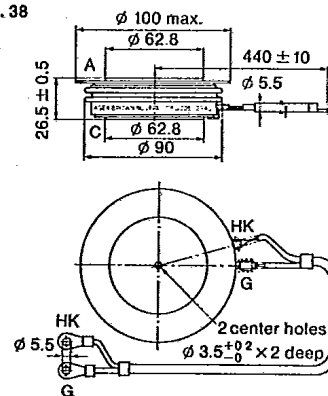


Fig. 41

Active part of a reverse conducting GTO thyristor with the diode at the rim.

Aktiv-Teil eines rückwärtsleitenden GTO-Thyristors mit Diode am Rand.

Partie actif d'une GTO thyristor à conduction inverse avec diode incorporé.